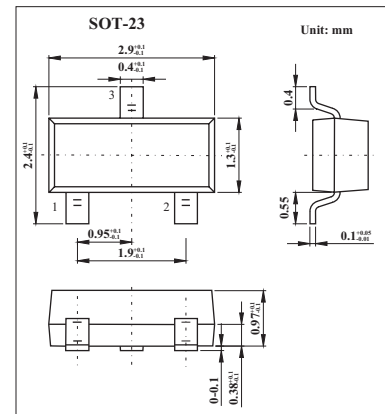


Shottky barrier diode

RB425D

■ Features

- Small mold type.(SMD3)
- Low IR.
- High reliability.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Limits	Unit
Reverse voltage (repetitive peak)	V_{RM}	40	V
DC reverse voltage	V_R	40	V
Average rectified forward current *	I_o	100	mA
Forward current surge peak (60 Hz 1cyc) *	I_{FSM}	1	A
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-40 to + 125	°C

* Rating of per diode

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	V_F	$I_F = 100 \text{ mA}$			0.55	V
		$I_F = 10 \text{ mA}$			0.34	V
Reverse current	I_R	$V_R = 10 \text{ V}$			30	μA
Capacitance between terminals	C_T	$V_R = 10 \text{ V}, f = 1.0 \text{ MHz}$		6.0		pF

■ Marking

Marking	D3L
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